

Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of <http://www.nxp.com>, <http://www.philips.com/> or <http://www.semiconductors.philips.com/>, use <http://www.nexperia.com>

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use salesaddresses@nexperia.com (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

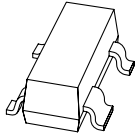
Should be replaced with:

- © **Nexperia B.V. (year). All rights reserved.**

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via salesaddresses@nexperia.com). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia



BCV61

NPN general-purpose double transistors

Rev. 04 — 18 December 2009

Product data sheet

1. Product profile

1.1 General description

NPN general-purpose double transistors in a small SOT143B Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package		PNP complement
	NXP	JEITA	
BCV61	SOT143B	-	BCV62
BCV61A			BCV62A
BCV61B			BCV62B
BCV61C			BCV62C

1.2 Features

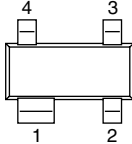
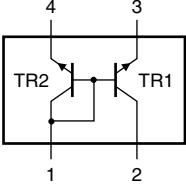
- Low current (max. 100 mA)
- Low voltage (max. 30 V)
- Matched pairs

1.3 Applications

- Applications with working point independent of temperature
- Current mirrors

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	collector TR2; base TR1 and TR2		
2	collector TR1		
3	emitter TR1		
4	emitter TR2		

006aaa842

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BCV61	-	plastic surface-mounted package; 4 leads	SOT143B
BCV61A			
BCV61B			
BCV61C			

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BCV61	1M*
BCV61A	1J*
BCV61B	1K*
BCV61C	1L*

- [1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transistor					
V_{CBO}	collector-base voltage	open emitter	-	30	V
V_{CEO}	collector-emitter voltage	open base	-	30	V
V_{EBS}	emitter-base voltage	$V_{CE} = 0$ V	-	6	V
I_C	collector current		-	100	mA
I_{CM}	peak collector current		-	200	mA
I_{BM}	peak base current		-	200	mA
Per device					
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	250	mW
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB).

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W

[1] Device mounted on an FR4 PCB.

7. Characteristics

Table 7. Characteristics

$T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
Transistor TR1							
I_{CBO}	collector-base cut-off current	$V_{CB} = 30\text{ V};$ $I_E = 0\text{ A}$	-	-	15	nA	
		$V_{CB} = 30\text{ V};$ $I_E = 0\text{ A};$ $T_j = 150\text{ °C}$	-	-	5	μA	
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V};$ $I_C = 0\text{ A}$	-	-	100	nA	
h_{FE}	DC current gain	$V_{CE} = 5\text{ V};$ $I_C = 100\text{ }\mu\text{A}$	100	-	-		
		$V_{CE} = 5\text{ V};$ $I_C = 2\text{ mA}$	110	-	800		
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA};$ $I_B = 0.5\text{ mA}$	-	90	250	mV	
		$I_C = 100\text{ mA};$ $I_B = 5\text{ mA}$	-	200	600	mV	
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA};$ $I_B = 0.5\text{ mA}$	[1]	700	-	mV	
		$I_C = 100\text{ mA};$ $I_B = 5\text{ mA}$	[1]	900	-	mV	
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA};$ $V_{CE} = 5\text{ V}$	[2]	580	660	700	mV
		$I_C = 10\text{ mA};$ $V_{CE} = 5\text{ V}$	[2]	-	-	770	mV
f_T	transition frequency	$V_{CE} = 5\text{ V};$ $I_C = 10\text{ mA};$ $f = 100\text{ MHz}$	100	-	-	MHz	
C_c	collector capacitance	$V_{CB} = 10\text{ V};$ $I_E = i_e = 0\text{ A};$ $f = 1\text{ MHz}$	-	2.5	-	pF	
NF	noise figure	$V_{CE} = 5\text{ V};$ $I_C = 200\text{ }\mu\text{A};$ $R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz};$ $B = 200\text{ Hz}$	-	-	10	dB	

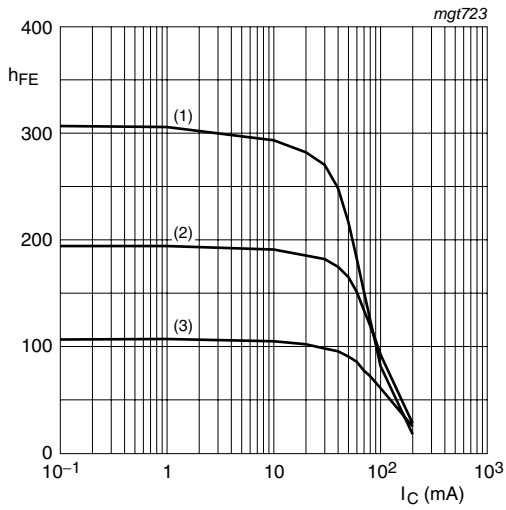
Table 7. Characteristics ...continued
 $T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Transistor TR2						
V_{EBS}	emitter-base voltage	$V_{CB} = 0\text{ V};$ $I_E = -250\text{ mA}$	-	-	-1.8	V
		$V_{CB} = 0\text{ V};$ $I_E = -10\text{ }\mu\text{A}$	-400	-	-	mV
h_{FE}	DC current gain	$V_{CE} = 5\text{ V};$ $I_C = 2\text{ mA}$				
		BCV61	110	-	800	
		BCV61A	110	-	220	
		BCV61B	200	-	450	
		BCV61C	420	-	800	
Transistors TR1 and TR2						
I_{C1}/I_{E2}	current matching	$I_{E2} = -0.5\text{ mA};$ $V_{CE1} = 5\text{ V}$				
		$T_{amb} \leq 25\text{ °C}$	0.7	-	1.3	
		$T_{amb} \leq 150\text{ °C}$	0.7	-	1.3	
I_{E2}	emitter current 2	$V_{CE1} = 5\text{ V}$	[3]	-	-5	mA

[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

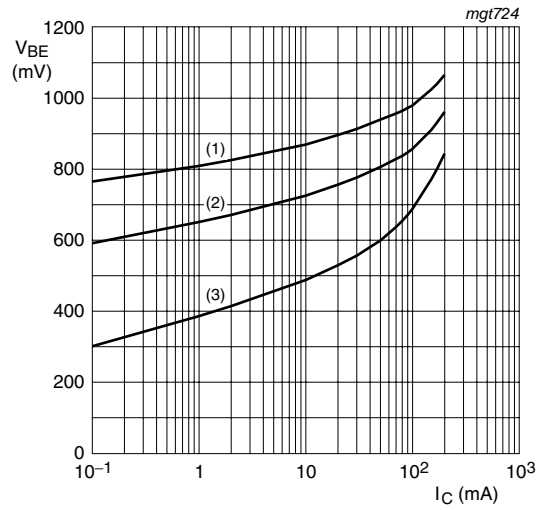
[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

[3] Device, without emitter resistors, mounted on an FR4 PCB.



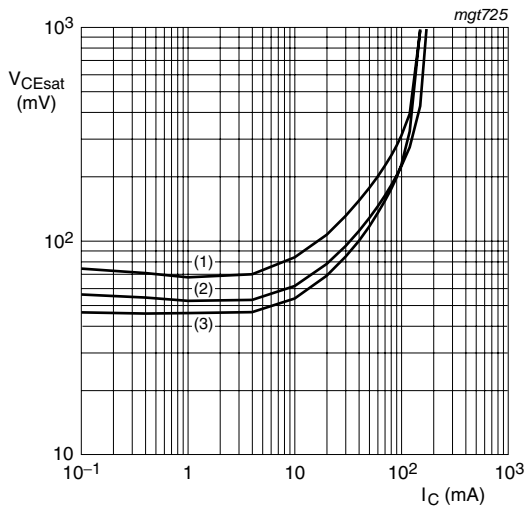
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 1. BCV61A: DC current gain as a function of collector current; typical values



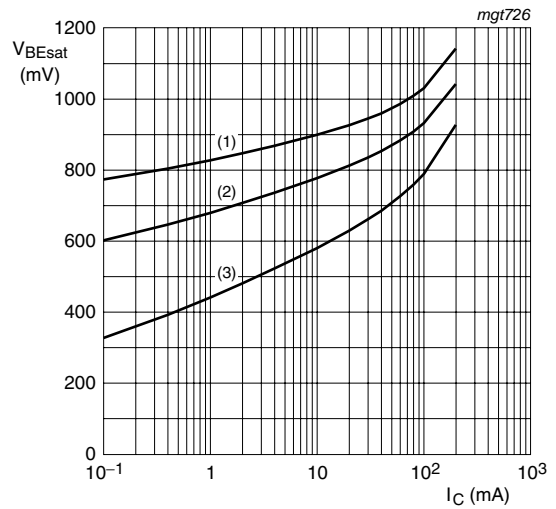
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 2. BCV61A: Base-emitter voltage as a function of collector current; typical values



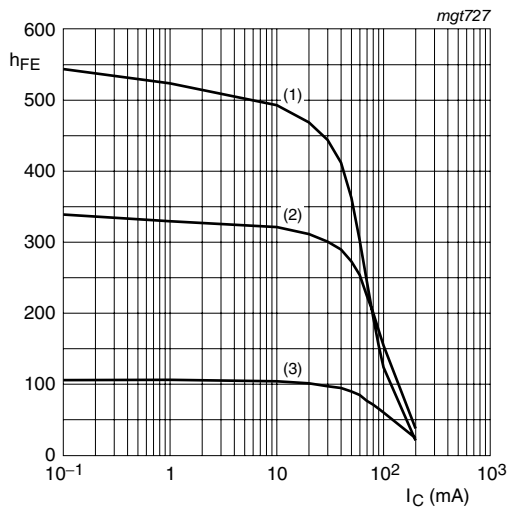
$I_C/I_B = 20$
 (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 3. BCV61A: Collector-emitter saturation voltage as a function of collector current; typical values



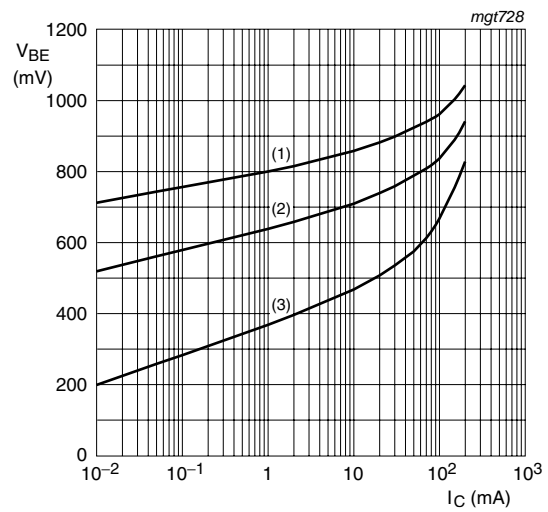
$I_C/I_B = 10$
 (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 4. BCV61A: Base-emitter saturation voltage as a function of collector current; typical values



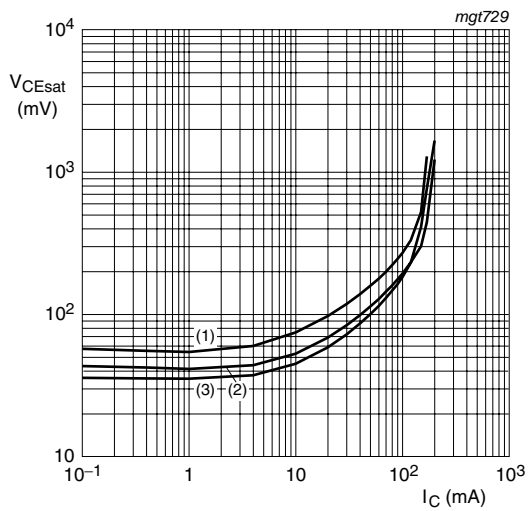
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 5. BCV61B: DC current gain as a function of collector current; typical values



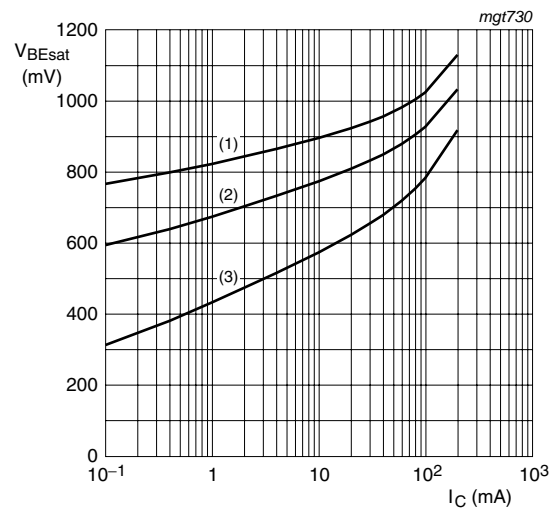
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 6. BCV61B: Base-emitter voltage as a function of collector current; typical values



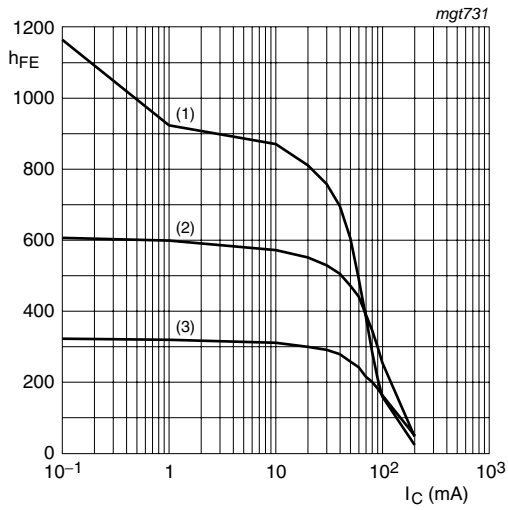
$I_C/I_B = 20$
 (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 7. BCV61B: Collector-emitter saturation voltage as a function of collector current; typical values



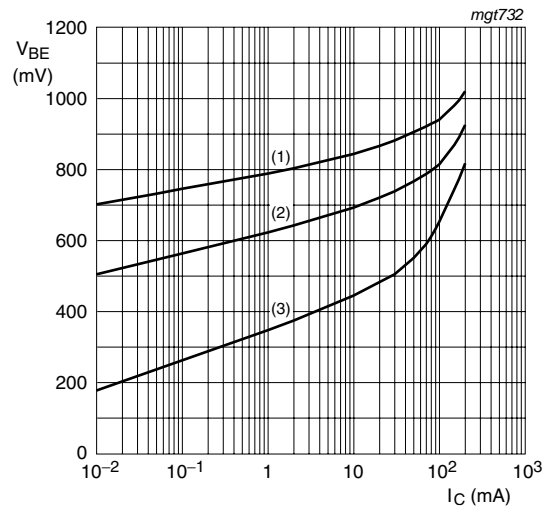
$I_C/I_B = 10$
 (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 8. BCV61B: Base-emitter saturation voltage as a function of collector current; typical values



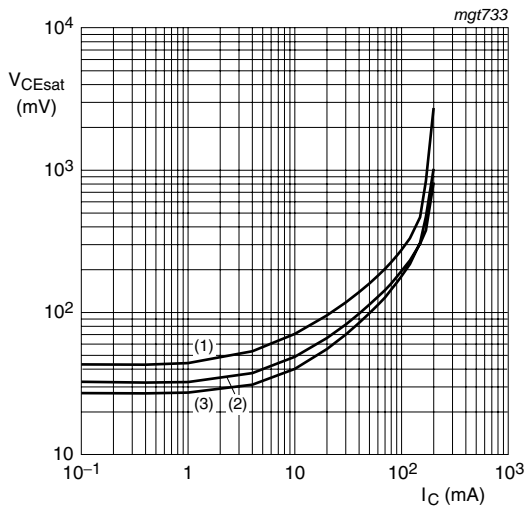
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 9. BCV61C: DC current gain as a function of collector current; typical values



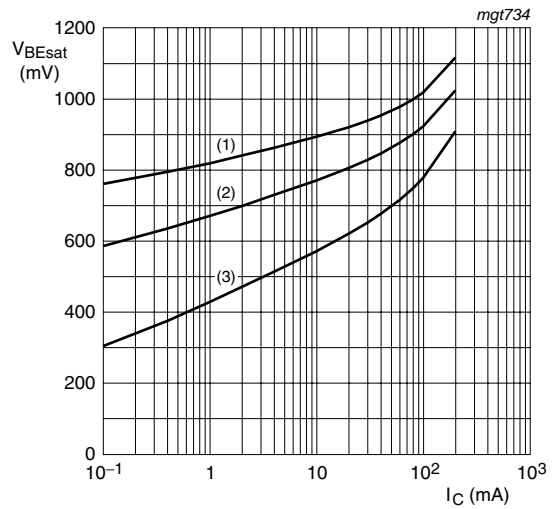
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig 10. BCV61C: Base-emitter voltage as a function of collector current; typical values



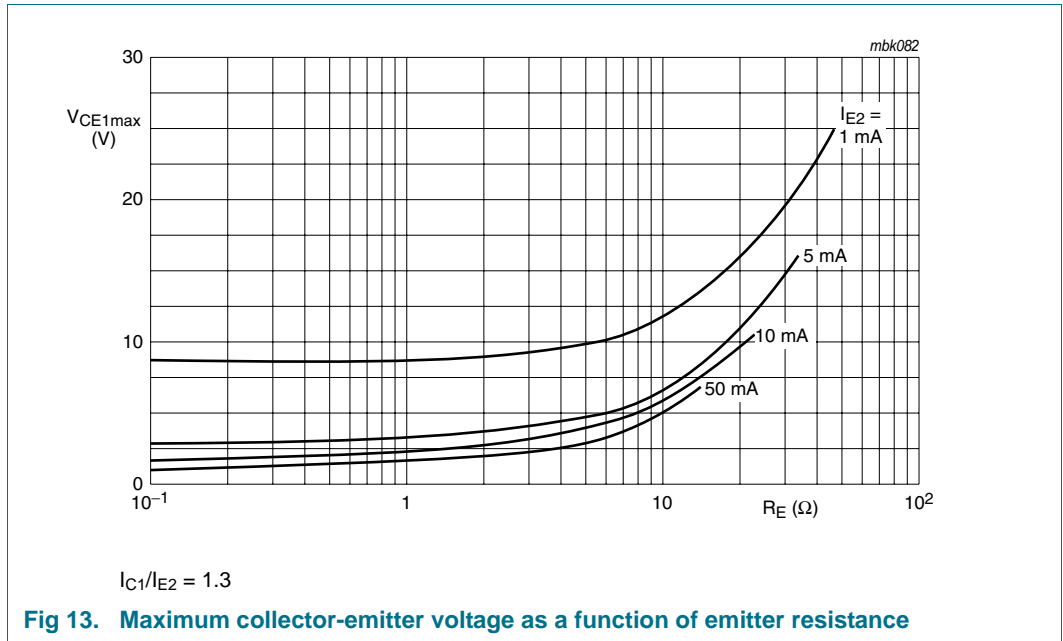
$I_C/I_B = 20$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 11. BCV61C: Collector-emitter saturation voltage as a function of collector current; typical values

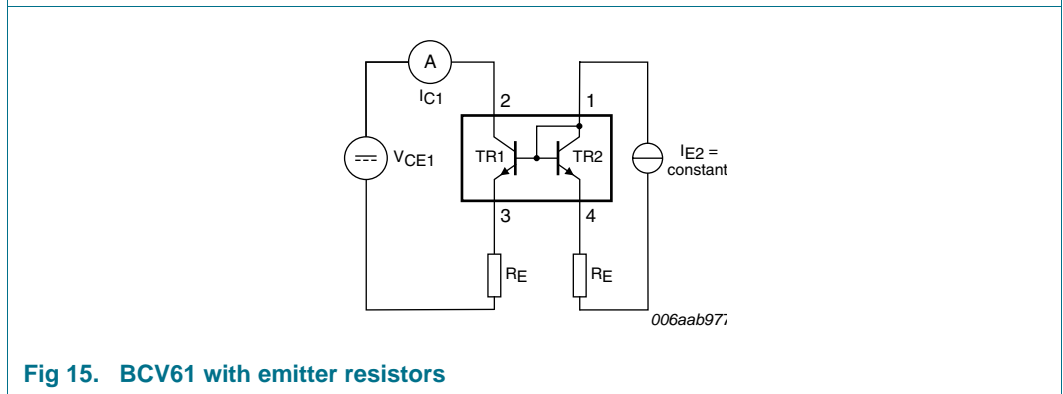
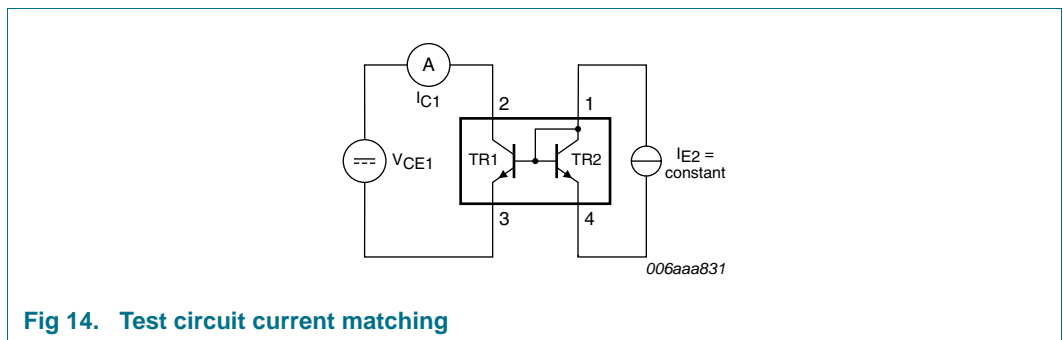


$I_C/I_B = 10$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig 12. BCV61C: Base-emitter saturation voltage as a function of collector current; typical values



8. Test information



9. Package outline

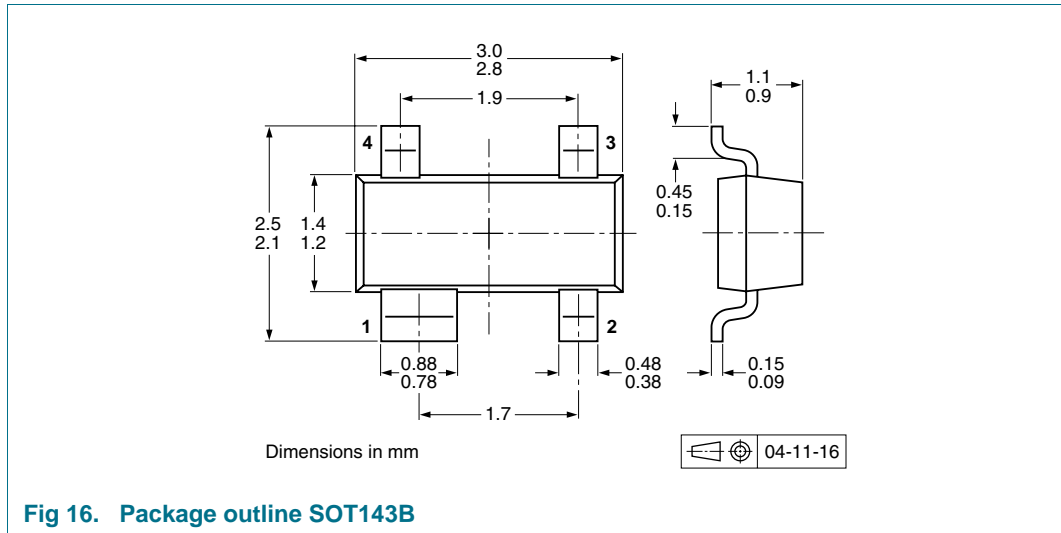


Fig 16. Package outline SOT143B

10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BCV61	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235
BCV61A				
BCV61B				
BCV61C				

[1] For further information and the availability of packing methods, see [Section 14](#).

11. Soldering

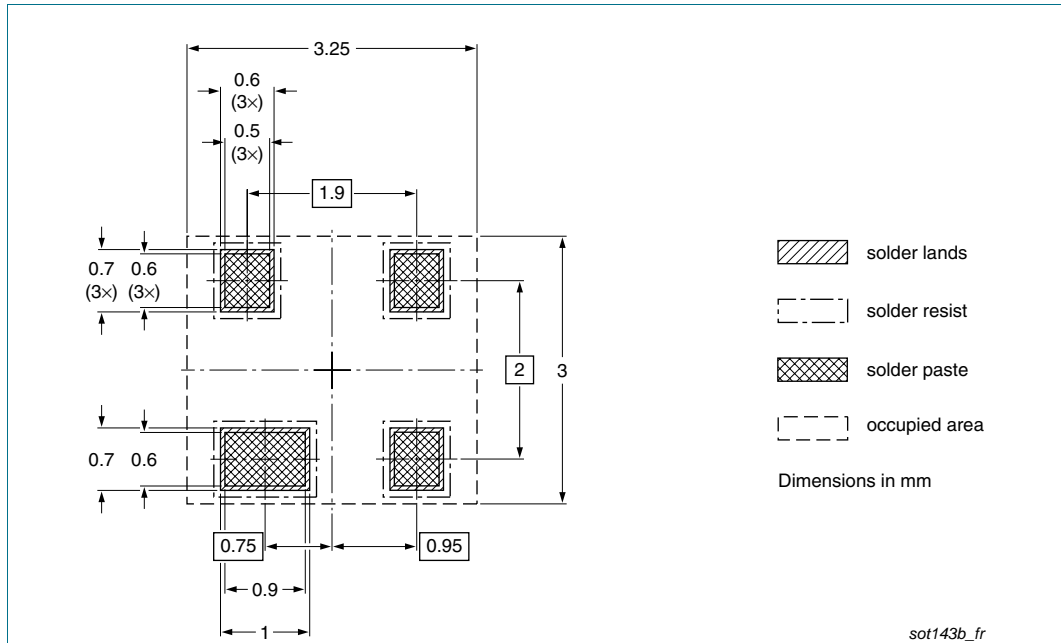


Fig 17. Reflow soldering footprint SOT143B

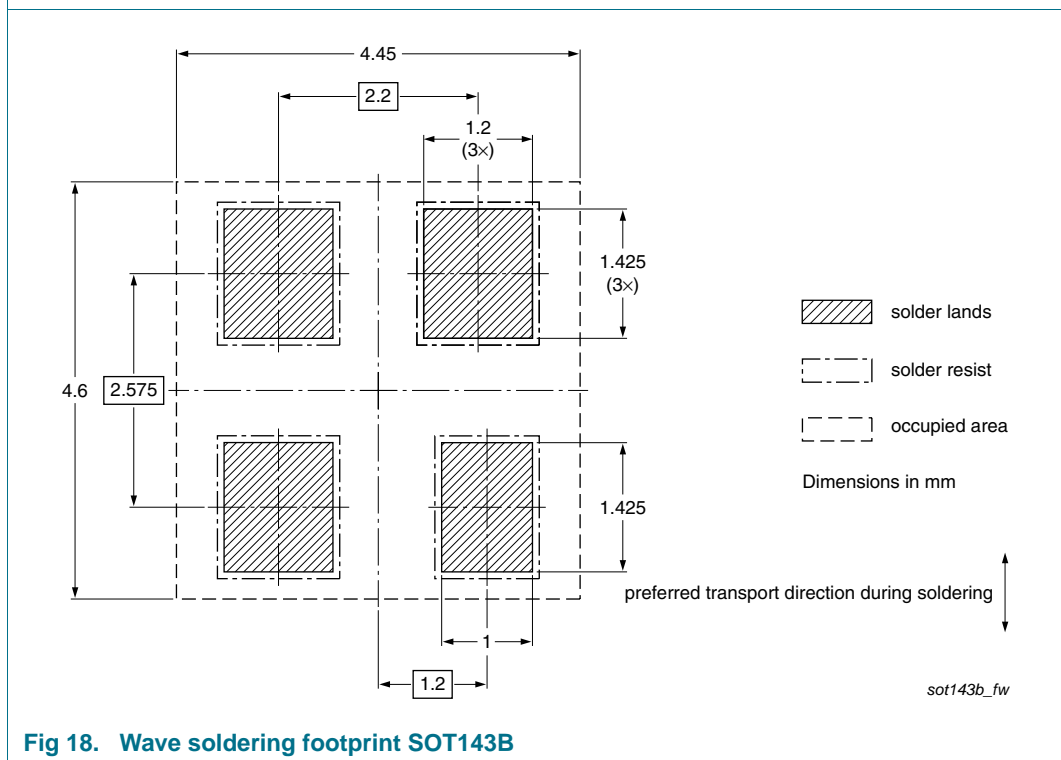


Fig 18. Wave soldering footprint SOT143B

12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BCV61_4	20091218	Product data sheet	-	BCV61_3
Modifications:		<ul style="list-style-type: none"> • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Section 3 "Ordering information": added • Section 4 "Marking": updated • Figure 1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11 and 12: added • Section 8 "Test information": added • Figure 16: superseded by minimized package outline drawing • Section 10 "Packing information": added • Section 11 "Soldering": added • Section 13 "Legal information": updated 		
BCV61_3	19990408	Product specification	-	BCV61_CNV_2
BCV61_CNV_2	19970616	Product specification	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

13.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

13.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental

damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

13.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

14. Contact information

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

15. Contents

1	Product profile	1
1.1	General description	1
1.2	Features	1
1.3	Applications	1
2	Pinning information	1
3	Ordering information	2
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	3
7	Characteristics	3
8	Test information	8
9	Package outline	9
10	Packing information	9
11	Soldering	10
12	Revision history	11
13	Legal information	12
13.1	Data sheet status	12
13.2	Definitions	12
13.3	Disclaimers	12
13.4	Trademarks	12
14	Contact information	12
15	Contents	13

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.



© NXP B.V. 2009.

All rights reserved.

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 18 December 2009

Document identifier: BCV61_4



**Стандарт
Электрон
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331